Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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GHz TECHNOLOGY
RF-MICROWAVE SILICON POWER TRANSISTORS

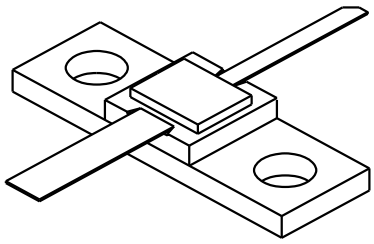
2224-6L

6 Watts, 22 Volts, Class C
Microwave 2200-2400 MHz

GENERAL DESCRIPTION

The 2224-6L is a COMMON BASE transistor capable of providing 6 Watts, Class C output power over the band 2200-2400 MHz. The transistor includes input prematching for full Broadband capability. Gold metalization and diffused ballasting are used to provide high reliability and supreme ruggedness. The transistor uses a fully hermetic High Temperature Solder Sealed package.

CASE OUTLINE
55LV STYLE 1



ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25ºC 22 Watts

Maximum Voltage and Current

BVces	Collector to Emitter Voltage	40 Volts
BVebo	Emitter to Base Voltage	3.5 Volts
Ic	Collector Current	1.25 Amps

Maximum Temperatures

Storage Temperature	- 40 to + 200ºC
Operating Junction Temperature	+ 200ºC

ELECTRICAL CHARACTERISTICS @ 25 ^{O}C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout	Power Out	F = 2200-2400 MHz	6.0			Watts
Pin	Power Input	Vcc = 22 Volts			1.2	Watts
Pg	Power Gain		7.0			dB
ηc	Efficiency			40		%
VSWR	Load Mismatch Tolerance	Pout = 6.0 Watts			10:1	

BVces	Collector to Emitter Breakdown	Ic = 10 mA	40			Volts
BVebo	Emitter to Base Breakdown	Ie = 5 mA	3.5			Volts
Hfe	Current Gain	Vce = 5 V, Ic = 1 A	20		120	
Cob	Output Capacitance	Vcb = 22 F = 1 MHz		7		pF
θjc	Thermal Resistance	Tc = 25ºC			8.0	ºC/W

Initial Issue December 15, 1994

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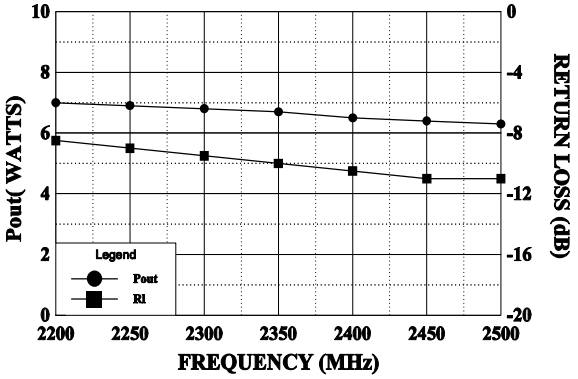
CHz TECHNOLOGY
RF-MICROWAVE SILICON POWER TRANSISTORS

2224-6L

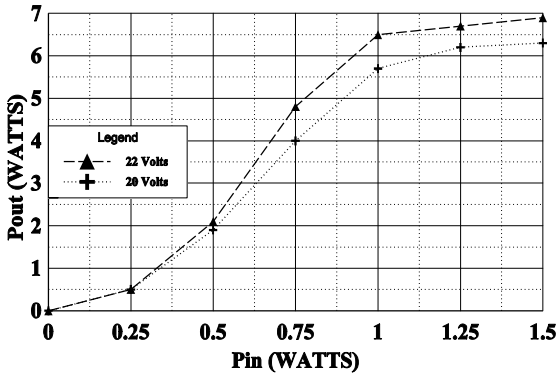
BROADBAND POWER OUT & RETURN LOSS

Pin = 1.2 Watts, Vcc = 22 Volts



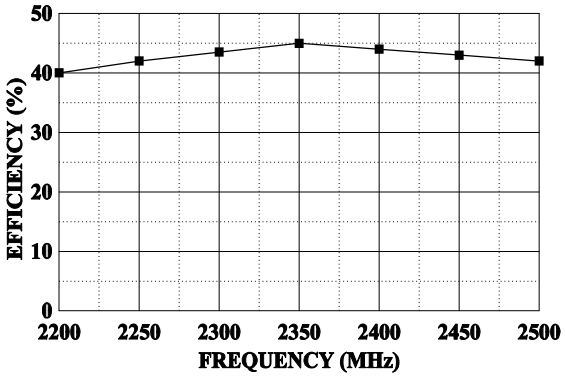
POWER OUTPUT vs POWER INPUT

Vcc - 20, 22 Volts



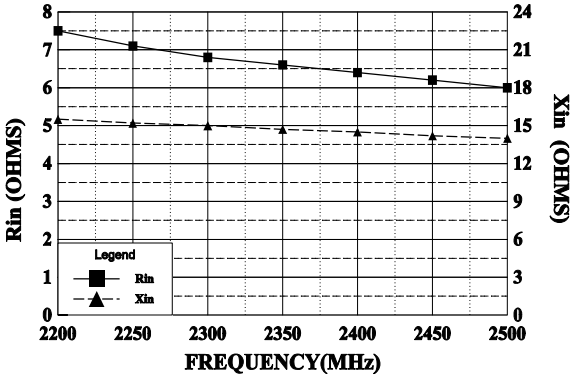
EFFICIENCY vs FREQUENCY

Vcc =22 Volts



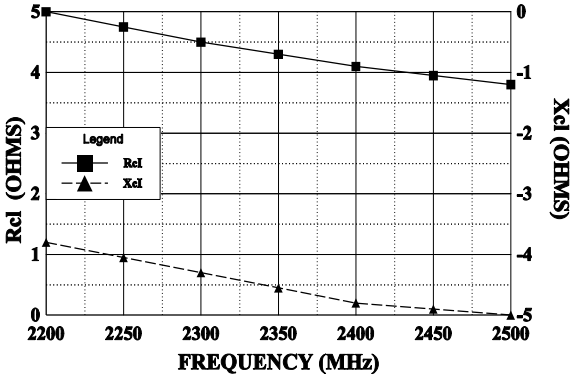
INPUT IMPEDANCE

Vcc = 22V, Pout = 6 W



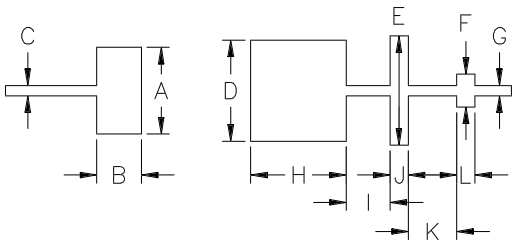
LOAD IMPEDANCE

Vcc = 22V, Pout = 6 W



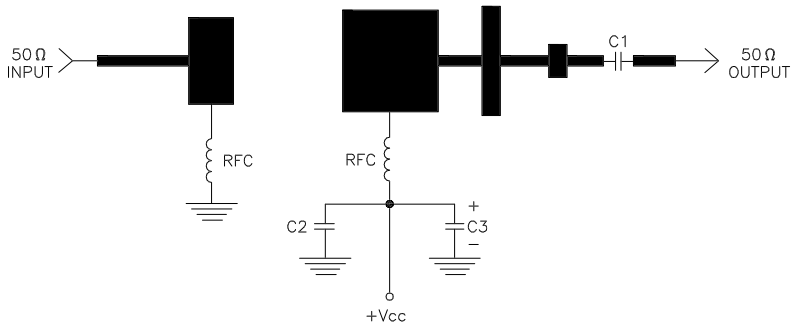
August 1996

REVISIONS				
ZONE	REV	DESCRIPTION	DATE	APPROVED



DIM	INCHES
A	.475
B	.245
C	.053
D	.555
E	.600
F	.180
G	.053
H	.525
I	.240
J	.100
K	.265
L	.100

2224-6L TEST CIRCUIT



DIELECTRIC = 20 MIL THICK TFE Er = 2.43
C1, C2 = 62pF CHIP ATC "B"
C3 = 10 MFD @ 35V
RFC = 4 turns #22 wire 1/16" I.D.

	CAGE	DWG NO.	REV
GHz TECHNOLOGY	0PJR2	2224-6L	A
		SCALE 1/1	SHEET